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I hereby certify that on the date specified below, this correspondence is being deposited with the United States Postal Service as first-class mail in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

June 30, 2006  
Date

Alexandra Beggs  
Alexandra Beggs

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant : Vishnu K. Agarwal

Attorney Docket No.: 501082.10

Patent No. : US 6,808,976 B1

Serial No. : 09/652,714

Issue Date : October 26, 2004

Filed : August 31, 2000

Title : DEVICE AND METHOD FOR PROTECTING AGAINST OXIDATION OF A  
CONDUCTIVE LAYER IN SAID DEVICE

**REQUEST FOR CERTIFICATE OF CORRECTION**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**Certificate**

**JUL 10 2006**

**of Correction**

Sir:

A Certificate of Correction under 35 U.S.C. § 254 is respectfully requested for the above-identified patent in order to correct Patent and Trademark Office errors made during the printing of the patent. The changes in the patent needed to correct the errors are as follows:

<u>Column, Line</u>	<u>Reads</u>	<u>Should Read</u>
Column 2, Line 9	"WN <sub>x</sub> /SiO <sub>2</sub> polysilicon"	--WN <sub>x</sub> /SiO <sub>2</sub> /polysilicon--
Column 2, Line 15	"WN <sub>x</sub> ,"	--WN <sub>x</sub> --
Column 3, Line 16	"In yet another"	--Yet another--
Column 6, Line 55	"tantalum pentoxide"	--the tantalum pentoxide--
Column 8, Line 1	"process describe above"	--processed described above--
Column 10, Line 59	[Omitted claims]	--27. The method in claim 22 further comprising depositing a

**JUL 10 2006**

plug on which the first conductive layer is thereafter deposited, and wherein exposing the second conductive layer to a thermal process comprises flowing the second conductive layer.

28. The method in claim 22, wherein exposing the conductive layer to a thermal process comprises exposing the conductive layer to an alloy process.--

The above errors for which correction is requested under 35 U.S.C. § 254 were made in the printing of the patent or in the original application. The errors are considered sufficiently important to justify the processing of a Certificate of Correction under 35 U.S.C. § 254. A Form PTO-1050, in duplicate, is enclosed herewith.

The Commissioner is hereby authorized to charge payment of any fees associated with this communication to Deposit Account No. 50-1266. A duplicate copy of this sheet is enclosed.

Favorable consideration of this Request is respectfully requested.

Respectfully submitted,

Date:

June 28, 2006

By:

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Enclosures:

Postcard

Form PTO-1050 (+ copy)

**UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION**

PATENT NO. : US 6,808,976 B1 *SN 09/632714*  
 DATED : October 26, 2004  
 INVENTOR(S) : Vishnu K. Agarwal

*476 1082*

It is certified that errors appear in the above identified patent and that said Letters Patent is hereby corrected as shown below:

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MAILING ADDRESS OF SENDER:

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Patent No. 6,808,976 B1

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FORM PTO-1050 (REV. 3-82)

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CERTIFICATE OF CORRECTION

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